

Title (en)

Device and method for comminution of semiconductive material

Title (de)

Vorrichtung und Verfahren zum Zerkleinern von Halbleitermaterial

Title (fr)

Dispositif et procédé de fragmentation de matériaux semiconducteur

Publication

EP 0887105 B1 20010905 (DE)

Application

EP 98110151 A 19980604

Priority

DE 19727441 A 19970627

Abstract (en)

[origin: EP0887105A1] Cutting up semiconductor material comprises direct current passage by pulsed high voltage application using electrodes which consist of the semiconductor material (preferably silicon) and which are made conductive by heating. Also claimed is the apparatus for carrying out the above process, including spaced electrodes (3) having heaters (5).

IPC 1-7

B02C 19/18; **B02C 19/12**; **B23H 9/00**; **B28D 5/00**

IPC 8 full level

B02C 19/18 (2006.01); **B23H 9/00** (2006.01); **B28D 5/00** (2006.01); **C30B 33/04** (2006.01); **H01L 21/304** (2006.01)

CPC (source: EP KR US)

B02C 19/0056 (2013.01 - EP US); **B02C 19/18** (2013.01 - EP KR US); **B28D 5/00** (2013.01 - EP US); **B02C 2019/183** (2013.01 - EP KR US)

Cited by

CN111632994A; WO2015143572A1

Designated contracting state (EPC)

DE IT

DOCDB simple family (publication)

EP 0887105 A1 19981230; **EP 0887105 B1 20010905**; CN 1209034 A 19990224; DE 19727441 A1 19990107; DE 59801370 D1 20011011; JP 2961694 B2 19991012; JP H1142635 A 19990216; KR 19990006851 A 19990125; TW 387823 B 20000421; US 6024306 A 20000215

DOCDB simple family (application)

EP 98110151 A 19980604; CN 98102651 A 19980624; DE 19727441 A 19970627; DE 59801370 T 19980604; JP 16723098 A 19980615; KR 19980021550 A 19980610; TW 87110208 A 19980624; US 10282998 A 19980623